

Zener Diode Chips (Dual Pad) for ESD Bidirectional Protection

1. Feature:

- 1-1 Silicon Zener diode chips for electrostatic discharge (ESD) protection application
- 1-2 This specification applies to N/P/N-Type silicon Zener diode chip (Dual pad/Vertical)
Device NO:WT-Z210V-AU4

2. Structure:

- 2-1 Planar type: Silicon Diode
- 2-2 Electrodes:
Top side : Gold Pad.(Cathode)
Back side : Gold Layer.(Anode)

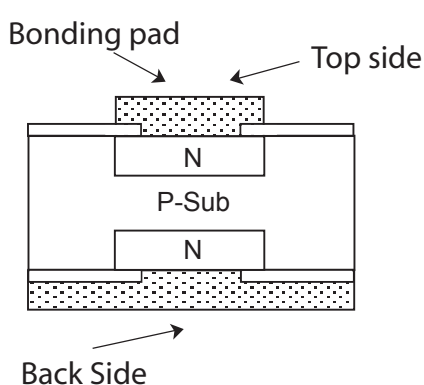
3. Size:

- 3-1 Chip size: 10.0 mils x 10.0 mils (254 um x 254 um).
- 3-2 Chip thickness: 4.0 ± 1.0 mils (100 ± 25.4 um).
- 3-3 Dual Bonding pad: 7.7 mils x 7.7mils (195um x 195um).
- 3-4 Pattern drawing: Refer to the attached drawing.

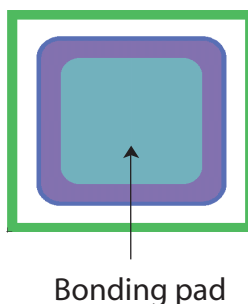
4. Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Zener Voltage	Vz(Top) Vz(Back)	Iz=5mA	5.8 5.4	- -	7.0 6.6	V
Forward Voltage	Vf	If=20mA			1.2	V
Reverse Leakage Current	IR	VR=4V			100	nA
Electrostatic Discharge	ESD	HBM MIL-STD 883	8.0			KV

5. Drawing:



(Top View)



6. Protection Circuit:

